Special Issue

Emerging GaN Circuits and Devices Design for Various Applications

Message from the Guest Editor

Gallium nitride semiconductors are power semiconductors that have recently emerged. GaN material represents the highest energy band gap and charge density among semiconductor materials. These characteristics allow GaN transistors to produce high output power densities at high frequencies. GaN-on-Si devices are also being actively researched due to their economic feasibility and possibility of integration with other silicon-based integrated circuits. In this Special Issue, we invite researchers to submit their original research or review articles that are concerned with “Emerging GaN Circuits and Devices Design for Various Applications”. **Topic** (1) GaN MMICs (2) High-power GaN amplifier modules (3) High-voltage GaN driver circuits for electric vehicles (4) Highly efficient GaN DC-DC/buck/boost converters (5) 5G-millimeter-wave GaN power amplifiers (6) Robust and highly linear GaN low noise amplifiers/mixers/switches/attenuators (7) 6G GaN IC applications

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Guest Editor

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Deadline for manuscript submissions

closed (15 August 2023)

Electronics

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Impact Factor 2.6
CiteScore 6.1

mdpi.com/si/153960

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Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guest-edited by leading experts in selected topics of interest.

Editor-in-Chief

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